

DDR3 DRAM Modules Evaluated with the AMD First Generation A-Series “Llano” Mobile APU

Introduction

This list contains DDR3 SO-DIMMs that have been evaluated by AMD and have shown reliable operation on the AMD internal reference platform. Testing included functional testing over voltage and temperature, as well as V_{REF} margining.

Purpose

As each mobile platform is different in design and characteristics, AMD cannot guarantee that a SO-DIMM contained in this list will work reliably in a specific mobile platform. The sole purpose of this list is to provide guidance with respect to creating the SO-DIMM test matrix a platform designer needs to validate the operation of a platform design. **It is the platform designer’s responsibility to completely test and verify operation of SO-DIMMs based on their own test process.**

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1600 @ 1.5V

SO-DDR3 Tested at 1600 DDR Rate 1.5V 1DIMM/Channel Configuration

Llano FS1

DIMM Module			DRAM Component				
Mfg	PN	Capacity	Mfg	PN	Rev	Capacity	Date Code
Elpida	EBJ20UF8BCS0-GN-F	2GB	Elpida	J2108BCSE-GN-F	C	2Gb	1047
	EBJ21UE8BFU0-GN-F	2GB		J1108BFBG-GN-F	F	1Gb	1047
	EBJ20UF8BDU0-GN-F	2GB		J2108BDBG-GN-F	D	2Gb	1151
	EBJ41UF8BDU0-GN-F	4GB		J2108BDBG-GN-F	D	2GB	1151
	EBJ40UG8BBU0-GN-F	4GB		J4208BBBG-GN-F	B	4Gb	1153
	EBJ41UF8BCS0-GN-F	4GB		J2108BCSE-GN-F	C	2Gb	1047
	EBJ81UG8BBU0-GN-F	8GB		J4208BBBG-GN-F	B	4Gb	1153
SK Hynix	HMT325S6CFR8C-PB N0	2GB	SK Hynix	H5TQ2G83CFR-PBC	C	2GB	126
	HMT351S6BFR8C-PB N0	4GB		H5TQ2G83BFR-PBC	B	2Gb	1102
	HMT451S6AFR8C-PB N0	4GB		H5TC4G83AFR-PBA	A	4Gb	*
	HMT41GS6MFR8C-PB N0	8GB		H5TQ4G83MFR-PBC	M	4Gb	1135
	HMT41GS6AFR8C-PB N0	8GB		H5TC4G83AFR-PBA	A	4Gb	*
Micron	MT8JSF25664HDZ-1G6D1	2GB	Micron	MT41J128M16HA-125:D	D	2Gb	1050
	MT16JTF25664HZ-1G6G1	2GB		MT41J128M8JP-125:G	G	1Gb	1102
	MT8JTF25664HZ-1G6M1	2GB		MT41K256M8DA-125:M	M	2Gb	1112
	MT8JTF25664HZ-1G6M1	2GB		MT41K256M8DA-125:M	M	2Gb	1112
	MT4JTF25664HZ-1G6E1	2GB		MT41K512M8RH-125:E	E	4Gb	na
	MT16JTF51264HZ-1G6M1	4GB		MT41K256M8DA-125:M	M	2Gb	1126
	MT8JTF51264HZ-1G6E1	4GB		MT41K512M8RH-125:E	E	4Gb	na
Nanya	NT1GC64BH4B0PS-DI	1GB	Nanya	NT5CB128M16BP-DI	B	2Gb	1107
	NT2GC64B88G0NS-DI	2GB		NT5CB256M8GN-DI	G	2Gb	1124
	NT4GC64B8HG0NS-DI	4GB		NT5CB256M8GN-DI	G	2Gb	1124
	NT4GC64B8HB0NS-DI	4GB		NT5CB256M8BN-DI	B	2Gb	1110
Samsung	M471B5773DH0-CK0	2GB	Samsung	K4B2G0846D-HCK0	D	2Gb	113
	M471B5773CHS-CK0	2GB		K4B2G0846C-HCK0	C	2GB	004
	M471B5273CH0-CK0	4GB		K4B2G0846C-HCK0	C	2Gb	146
	M471B5273DH0-CK0	4GB		K4B2G0846D-HCK0	D	2Gb	140
	M471B1G73BH0-CK0	8GB		K4B4G0846B-HCK0	B	4Gb	146
PSC	AS8F8K83C-GN2E	2GB	PSC	A3P2GF3CKF-GGNAQ	C	2Gb	217M9E0G
	AS9F8L93B-GN2E	4GB		A3P4GF3BLF-GGNAF	B	4Gb	216M6B01
	ASAF8L93B-GN2E	8GB		A3P4GF3BLF-GGNAF	B	4Gb	216M6B02

BOLD = New Entry

1333 @ 1.5V

SO-DDR3 Tested at 1333 DDR Rate 1.5V 1DIMM/Channel Configuration

Llano FS1

DIMM Module			DRAM Component				
Mfg	PN	Capacity	Mfg	PN	Rev	Capacity	Date Code
A-Data	HY731B0873ZS	2GB	SK Hynix	H5TQ2G83BFR-H9C	B	2Gb	1031
	HY731C1674ZS	4GB		H5TQ2G83BFR-H9C	B	2Gb	1031
	MI74C1B0873Z2	2GB	Micron	MT41K256M8DA-125:M	M	2Gb	1150
	MI74C1C167HZ2	4GB		MT41K256M8DA-125:M	M	2Gb	1150
	AM1U16BC2P1	2GB	Elpida	3CCD-1211A	D	2Gb	U150
	AM1U16BC4P2	4GB		3CCD-1211A	D	2Gb	U150
Asint	SSY3128M8-EDJEF	1GB	Elpida	J1108BFBG-DJ-F	F	1Gb	na
Elixir	M2S1G64CBH4B5P-CG	1GB	Nanya	N2CB2G16BP-CG	B	2Gb	1045
	M2S2G64CB88B5N-CG	2GB		N2CB2G80BN-CG	B	2Gb	1051
	M2S4G64CB8HB5N-CG	4GB		N2CB2G80BN-CG	B	2Gb	1046
Elpida	EBJ21UE8BFU0-DJ-F	2GB	Elpida	EDJ1108BFBG-DJ-F	F	1Gb	1012
	EBJ20UF8BCS0-DJ-F	2GB		EDJ2108BCSE-DJ-F	C	2Gb	1032
	EBJ20UF8BDU0-DJ-F	2GB		EDJ2108BDBG-DJ-F	D	2Gb	1149
	EBJ41UF8BDU0-DJ-F	4GB		EDJ2108BDBG-DJ-F	D	2Gb	1146
	EBJ41UF8BCS0-DJ-F	4GB		EDJ2108BCSE-DJ-F	C	2Gb	1032
	EBJ40UG8BBU0-DJ-F	4GB		EDJ4208BBBG-GN-F	B	4Gb	1153
	EBJ81UG8BAS0-DJ-F	8GB		EDJ4208BASE-DJ-F	A	4Gb	1036
	EBJ81UG8BBU0-DJ-F	8GB		EDJ4208BBBG-GN-F	B	4Gb	1153
	SK Hynix	HMT312S6BFR6C-H9 N0		1GB	SK Hynix	H5TQ2G63BFR-H9C	B
HMT112S6DFR8C-H9 N0		1GB	H5TQ1G83DFR-H9C	D		1Gb	1026
HMT112S6TFR8C-H9 N0		1GB	H5TQ1G83TFR-H9C	T		1Gb	948
HMT325S6BFR8C-H9 N0		2GB	H5TQ2G83BFR-H9C	B		2Gb	1007
HMT351S6CFR8C-H9 N0		4GB	H5TQ2G83CFR-H9C	C		2Gb	102
HMT351S6BFR8C-H9 N0		4GB	H5TQ2G83BFR-H9C	B		2Gb	1009
Kingston	ACR128x64D3S1333C9	1GB	Elpida	D1288JELDPGD9U	D	1Gb	1022
	ACR256x64D3S1333C9	2GB		D1288JELDPGD9U	D	1Gb	1037
	KVR1333D3S9/2G	2GB		J1108BFSE-DJ-F	F	1Gb	1044
Micron	MT4JSF12864HZ-1G4D1	1GB	Micron	MT41J128M16HA-15E:D	D	2Gb	1022
	MT8JTF25664HZ-1G4M1	2GB		MT41K256M8DA-125:M	M	2Gb	1112
	MT8JSF25664HZ-1G4D1	2GB		MT41J256M8HX-15E:D	D	2Gb	1022
	MT16JSF51264HZ-1G4D1	4GB		MT41J256M8HX-15E:D	D	2Gb	1022
	MT16JTF51264HZ-1G4M1	4GB		MT41K256M8DA-125:M	M	2Gb	1114
	MT16JTF1G64HZ-1G6E1	8GB		MT41K512M8RH-125:E	E	4Gb	1308
Nanya	NT1GC64BH4B0PS-CG	1GB	Nanya	NT5CB128M16BP-CG	B	2Gb	1029
	NT2GC64B88B0NS-CG	2GB		NT5CB256M8BN-CG	B	2Gb	1023
	NT2GC64B88G0NS-CG	2GB		NT5CB256M8GN-CG	G	2Gb	1121
	NT4GC64B88B0NS-CG	4GB		NT5CB256M8BN-CG	B	2Gb	1023
Ramaxel	RMT1910MD66E7F-1333	1GB	Micron	MT41J128M16HA-15E:D	D	2Gb	1010
	RMT3150ED58E8W-1600	2GB		EDJ2108BDBG-GN-F	D	2Gb	1143
	RMT3010EC58E8F-1333	2GB		EDJ2108BCSE-DJ-F	C	2Gb	1128
	RMT3160ED58E9W-1600	4GB	Elpida	EDJ2108BDBG-GN-F	D	2Gb	1206
	RMT3020EC58E9F-1333	4GB		EDJ2108BCSE-DJ-F	C	2Gb	1128
Samsung	M471B2873FHS-CH9	1GB	Samsung	K4B1G0846F-HCH9	F	1Gb	1001
	M471B5773CHS-CH9	2GB		K4B2G0846C-HCH9	C	2Gb	943
	M471B5673FHO-CH9	2GB		K4B1G0846F-HCH9	F	1Gb	1001
	M471B5273CHO-CH9	4GB		K4B2G0846C-HCH9	C	2Gb	943
Sharetronic	SY321NG08HBF	1GB	SK Hynix	H5TQ1G83DFR-H9C	D	1Gb	1023

BOLD = New Entry

1333 @ 1.35V

SO-DDR3 Tested at 1333 DDR Rate 1.35V 1DIMM/Channel Configuration

Llano FS1

DIMM Module			DRAM Component				
Mfg	PN	Capacity	Mfg	PN	Rev	Capacity	Date Code
Elpida	EBJ41UF8EDU0-DJ-F	4GB	Elpida	EDJ2108EDBG-DJ-F	D	2Gb	1145
	EBJ20UF8EDU0-DJ-F	4GB		EDJ2108EDBG-DJ-F	D	2Gb	1145
	EBJ40UG8EBU0-DJ-F	4GB		EDJ4208EBBG-DJ-F	B	4Gb	1204
	EBJ40UG8EBU0-GN-F	4GB		EDJ4208EBBG-GN-F	B	4Gb	1206
	EBJ40UG8EFU0-GN-F	4GB		EDJ4208EFBG-GN-F	F	2Gb	1228
	EBJ81UG8EFU0-GN-F	8GB		EDJ4208EFBG-GN-F	F	4Gb	1229
	EBJ81UG8EBU0-DJ-F	8GB		EDJ4208EBBG-DJ-F	B	4Gb	1204
	EBJ81UG8EBU0-GN-F	8GB		EDJ4208EBBG-GN-F	B	4Gb	1206
SK Hynix	HMT325S6CFR8A-H9 N0	2GB	SK Hynix	H5TC2G83CFR-H9A	C	2Gb	136
	HMT325S6EFR8A-PB N0	2GB		H5TC2G83EFR-PBA	E	2Gb	na
	HMT325S6BFR8A-PB N0	2GB		H5TC2G83BFR-PBA	B	2Gb	1110
	HMT325S6BFR8A-PB N0	2GB		H5TC2G83BFR-PBA	B	2Gb	1110
	HMT425S6AFR6A-PB N0	2GB		H5TC4G63AFR-PBA	A	4Gb	1245
	HMT351S6EFR8A-PB N0	4GB		H5TC2G83EFR-PBA	E	2Gb	na
	HMT351S6CFR8A-PB N0	4GB		H5TC2G83CFR-PBA	C	2Gb	130
	HMT451S6AFR8A-PB N0	4GB		H5TC4G83AFR-PBA	A	4Gb	1244
	HMT41GS6MFR8A-PB N0	8GB		H5TC4G83MFR-PBA	M	4Gb	143
HMT41GS6AFR8A-PB N0	8GB	H5TC4G83AFR-PBA	A	4Gb	1242		
Micron	MT8KTF12864HDZ-1G4G1	1GB	Micron	MT41K64M16JT-15E:G	G	1Gb	1118
	MT4KTF12864HZ-1G4K1	1GB		MT41K256M8DA-125:K	K	2Gb	na
	MT4KTF12864HZ-1G6K1	1GB		MT41K128M16JT-125	K	1Gb	1228
	MT8KTF25664HZ-1G4M1	2GB		MT41K256M8DA-125:M	M	2Gb	1112
	MT8KTF25664HZ-1G4K1	2GB		MT41K256M8DA-125:K	K	2Gb	na
	MT4KTF25664HZ-1G4E1	2GB		MT41K512M8RH-125:E	E	4Gb	na
	MT8KTF25664HZ-1G6M1	2GB		MT41K256M8DA-125:M	M	2Gb	1128
	MT8KTF25664HZ-1G6K1	2GB		MT41K256M8DA-125:K	K	2Gb	na
	MT4KTF25664HZ-1G6E1	2GB		MT41K512M8RH-125:E	E	4Gb	na
	MT16KTF51264HZ-1G4M1	4GB		MT41K256M8DA-125:M	M	2Gb	1114
	MT16KTF51264HZ-1G4K1	4GB		MT41K256M8DA-125:K	K	2Gb	na
	MT8KTF51264HZ-1G4E1	4GB		MT41K512M8RH-125:E	E	4Gb	na
	MT16KTF51264HZ-1G6M1	4GB		MT41K256M8DA-125:M	M	2Gb	1112
	MT16KTF51264HZ-1G6K1	4GB		MT41K256M8DA-125:K	K	2Gb	na
	MT8KTF51264HZ-1G6E1	4GB		MT41K512M8RH-125:E	E	4Gb	na
	MT16KTF51264HZ-1G6M1	4GB		MT41K256M8DA-125:M	M	2Gb	1112
	MT16KTF1G64HZ-1G4E1	8GB		MT41K512M8RH-125:E	E	4Gb	na
	MT16KTF1G64HZ-1G6D1	8GB		MT41K512M8RA-125:D	D	4Gb	1132
MT16KTF1G64HZ-1G6E1	8GB	MT41K512M8RH-125:E	E	4Gb	na		
Nanya	NT2GC64C88G0NS-DI	2GB	Nanya	NT5CC256M8GN-DI	G	2Gb	1140
	NT4GC64C8HG0NS-DI	4GB		NT5CC256M8GN-DI	G	2Gb	1140
Samsung	M471B5773CHS-YK0	2GB	Samsung	K4B2G0846C-HYK0	C	2Gb	216
	M471B5273CHO-YK0	4GB		K4B2G0846C-HYK0	C	2Gb	216
	M471B5273DH0-YK0	4GB		K4B2G0846D-HYK0	C	2Gb	222
	M471B5173CB0-YK0	4GB		K4B2G0846C-BYK0	C	2Gb	na
Sharetronic	SM321NH08IAF	2GB	Micron	MT41K256M8DA-125	M	2Gb	1150
	SM322NQ08IAF	4GB		MT41K256M8DA-125	M	2Gb	1150

BOLD = New Entry

1066 @ 1.5V

SO-DDR3 Tested at 1066 DDR Rate 1.5V 1DIMM/Channel Configuration

DIMM Module			DRAM Component				
Mfg	PN	Capacity	Mfg	PN	Rev	Capacity	Date Code
Elpida	EBJ10UE8BDS0-AE-F	1GB	Elpida	J1108BDSE-AE-F	D	1Gb	917
	EBJ21UE8BDS0-AE-F	2GB		J1108BDSE-AE-F	D	1Gb	941
Samsung	M471B2873FHS-CF8	1GB	Samsung	K4B1G0846F-HCF8	F	1Gb	1005
	M471B5273CH0-CF8	4GB		K4B2G0846C-HCF8	C	2Gb	952
	M471B5273BH1-CF8	4GB		K4B2G0846B-HCF8	B	2Gb	928

BOLD = New Entry

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